

Didier Chaussende

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

135
papers

1,283
citations

19
h-index

30
g-index

137
ext. papers

1,403
ext. citations

1.6
avg, IF

4.08
L-index

#	Paper	IF	Citations
135	A sessile drop approach for studying 4H-SiC/liquid silicon high-temperature interface reconstructions. <i>Journal of Materials Science</i> , 2022 , 57, 972	4.3	1
134	In Situ Interferometry for ppm-Order Solubility Analysis at High Temperatures: A Case Study of Carbon Solubility in Molten Silicon. <i>Metallurgical and Materials Transactions B: Process Metallurgy and Materials Processing Science</i> , 2021 , 52, 2619	2.5	
133	3C $\sqrt{3}$ 4H $\sqrt{3}$ and 6H $\sqrt{3}$ SiC crystal habitus and interfacial behaviours in high temperature Si-based solvents. <i>CrystEngComm</i> , 2020 , 22, 3489-3496	3.3	1
132	SiC/Al ₄ SiC ₄ -Based Heterostructure Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 3001-3007	4	1
131	Revisiting the Site-Competition Doping of 4H-SiC: Cases of N and Al. <i>Materials Science Forum</i> , 2020 , 1004, 96-101	0.4	
130	Monte Carlo Simulations of Electron Transport Characteristics of Ternary Carbide Al ₄ SiC ₄ . <i>ACS Applied Energy Materials</i> , 2019 , 2, 715-720	6.1	2
129	Structural, Electronic and Vibrational Properties of Al ₄ C ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1900037	1.3	3
128	Understanding Al incorporation into 4H-SiC during epitaxy. <i>Journal of Crystal Growth</i> , 2019 , 507, 338-343	1.6	3
127	Silicon carbide 2019 , 129-179		5
126	The (001) 3C SiC surface termination and band structure after common wet chemical etching procedures, stated by XPS, LEED, and HREELS. <i>Applied Surface Science</i> , 2018 , 427, 480-485	6.7	14
125	A new model for in situ nitrogen incorporation into 4H-SiC during epitaxy. <i>Scientific Reports</i> , 2017 , 7, 43069	4.9	13
124	(001) 3C SiC/Ni contact interface: In situ XPS observation of annealing induced Ni ₂ Si formation and the resulting barrier height changes. <i>Applied Surface Science</i> , 2017 , 400, 6-13	6.7	9
123	Vaporization and condensation in the Al ₄ C ₃ -SiC system. <i>Journal of the European Ceramic Society</i> , 2017 , 37, 4475-4482	6	8
122	Effect of Aluminum during the High Temperature Solution Growth of Si-Face 4H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 37-40	0.4	2
121	Experimental Investigation of the Seeding Stage during SiC Solution Growth Using Si and Al-Si Solvents. <i>Materials Science Forum</i> , 2016 , 858, 81-84	0.4	1
120	A first step toward bridging silicon carbide crystal properties and physical chemistry of crystal growth. <i>CrystEngComm</i> , 2016 , 18, 2119-2124	3.3	7
119	Analysis of Macrostep Formation during Top Seeded Solution Growth of 4H-SiC. <i>Crystal Growth and Design</i> , 2016 , 16, 3231-3236	3.5	9

118	Photoelectrical Parameters of a PVT Grown Bulk 15R-SiC Crystal at Different Stages of Growth. <i>Materials Science Forum</i> , 2015 , 821-823, 253-256	0.4	
117	Nitrogen Incorporation during Seeded Sublimation Growth of 4H-SiC and 6H-SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 60-63	0.4	2
116	Assessment of SiC Crystal Chemistry during the PVT Growth Process: Coupled Numerical Modeling and Thermodynamics Approach. <i>Materials Science Forum</i> , 2015 , 821-823, 96-99	0.4	
115	Synthesis and Characterization of Al ₄ SiC ₄ : A New Wide Band Gap Semiconductor Material. <i>Materials Science Forum</i> , 2015 , 821-823, 974-977	0.4	5
114	Macroscopic Approach to the Nucleation and Propagation of Foreign Polytype Inclusions during Seeded Sublimation Growth of Silicon Carbide. <i>Crystal Growth and Design</i> , 2015 , 15, 156-163	3.5	2
113	Open Issues in SiC Bulk Growth. <i>Materials Science Forum</i> , 2014 , 778-780, 3-8	0.4	3
112	Interaction between Vapor Species and Graphite Crucible during the Growth of SiC by PVT. <i>Materials Science Forum</i> , 2014 , 778-780, 31-34	0.4	1
111	Effect of Facet Occurrence on Polytype Destabilization during Bulk Crystal Growth of SiC by Seeded Sublimation. <i>Materials Science Forum</i> , 2014 , 778-780, 13-16	0.4	3
110	Ge Mediated Surface Preparation for Twin Free 3C-SiC Nucleation and Growth on Low Off-Axis 4H-SiC Substrate. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P285-P292	2	8
109	Comparison of Thermodynamic Databases for the Modeling of SiC Growth by PVT. <i>Materials Science Forum</i> , 2014 , 778-780, 35-38	0.4	1
108	Spiral Step Dissociation on PVT Grown SiC Crystals. <i>Materials Science Forum</i> , 2014 , 778-780, 39-42	0.4	1
107	Nondestructive Evaluation of Photoelectrical Properties of a PVT Grown Bulk 15R-SiC Crystal. <i>Materials Science Forum</i> , 2014 , 806, 65-69	0.4	1
106	Double-Position-Boundaries Free 3C-SiC Epitaxial Layers Grown on On-Axis 4H-SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P75-P81	2	15
105	Electromagnetic Enhancement of Carbon Transport in SiC Solution Growth Process: A Numerical Modeling Approach. <i>Materials Science Forum</i> , 2014 , 778-780, 71-74	0.4	7
104	Interface Shape: A Possible Cause of Polytypes Destabilization during Seeded Sublimation Growth of 15R-SiC. <i>Materials Science Forum</i> , 2014 , 806, 61-64	0.4	4
103	On Photoelectrical Properties of 6H-SiC Bulk Crystals PVT-Grown on 6H- and 4H-SiC Substrates. <i>Materials Science Forum</i> , 2014 , 778-780, 305-308	0.4	3
102	Ge Assisted SiC Epitaxial Growth by CVD on SiC Substrate. <i>Materials Science Forum</i> , 2014 , 778-780, 187-192		5
101	3C-SiC Heteroepitaxy on Hexagonal SiC Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 257-262	0.4	6

100	Comparison of the spiral growth modes of silicon-face and carbon-face silicon carbide crystals. <i>Journal of Crystal Growth</i> , 2013 , 384, 129-134	1.6	6
99	High temperature solution growth and characterization of Cr ₂ AlC single crystals. <i>Journal of Crystal Growth</i> , 2013 , 384, 88-95	1.6	34
98	Revealing the electronic band structure of trilayer graphene on SiC: An angle-resolved photoemission study. <i>Physical Review B</i> , 2013 , 88,	3.3	61
97	Epitaxial graphene morphologies probed by weak (anti)-localization. <i>Journal of Applied Physics</i> , 2013 , 113, 083715	2.5	7
96	Absence of Back Stress Effect in the PVT Growth of 6H Silicon Carbide. <i>Materials Science Forum</i> , 2013 , 740-742, 48-51	0.4	
95	Polytypic transformations in SiC: Diffuse x-ray scattering and Monte Carlo simulations. <i>Physical Review B</i> , 2013 , 88,	3.3	6
94	Diffuse X-ray scattering from partially transformed 3C-SiC single crystals. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 284, 19-22	1.2	2
93	Modeling of the Growth Rate during Top Seeded Solution Growth of SiC Using Pure Silicon as a Solvent. <i>Crystal Growth and Design</i> , 2012 , 12, 909-913	3.5	20
92	Combined experimental and computational study of the recrystallization process induced by electronic interactions of swift heavy ions with silicon carbide crystals. <i>Physical Review B</i> , 2012 , 86,	3.3	69
91	Critical assessment of birefringence imaging of dislocations in 6H silicon carbide. <i>Journal of Crystal Growth</i> , 2012 , 354, 202-207	1.6	6
90	Large Area Quasi-Free Standing Monolayer Graphene on 3C-SiC(111). <i>Materials Science Forum</i> , 2012 , 717-720, 617-620	0.4	3
89	Fabrication of SiC Nanopillars by Inductively Coupled SF ₆ /O ₂ Plasma. <i>Materials Science Forum</i> , 2012 , 711, 66-69	0.4	2
88	On the Stability of 3C-SiC Single Crystals at High Temperatures. <i>Materials Science Forum</i> , 2012 , 717-720, 493-496	0.4	
87	Growth Rate Prediction in SiC Solution Growth Using Silicon as Solvent. <i>Materials Science Forum</i> , 2012 , 717-720, 69-72	0.4	2
86	Application of an axial next-nearest-neighbor Ising model to the description of Mn _n +1AX _n phases. <i>Physical Review B</i> , 2012 , 85,	3.3	2
85	Identification of the Basal Plane Component of the Burgers Vector of Small Dislocations in 6H SiC Using Birefringence Microscopy. <i>Materials Science Forum</i> , 2012 , 717-720, 331-334	0.4	
84	Raman scattering from Ti ₃ SiC ₂ single crystals. <i>Applied Physics Letters</i> , 2011 , 98, 081912	3.4	40
83	Growth and Characterization of Thick Polycrystalline AlN Layers by HTCVD. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H328	3.9	7

82	Optical Investigation of Defect Filtering Effects in Bulk 3C-SiC Crystals Grown by the CF-PVT Method Using a Necking Technique. <i>Materials Science Forum</i> , 2011 , 679-680, 169-172	0.4	
81	Formation process of 3C-SiC on 6H-SiC (0001) by low-temperature solution growth in Si-Ge system. <i>Journal of Crystal Growth</i> , 2011 , 335, 94-99	1.6	15
80	Investigation on AlN epitaxial growth and related etching phenomenon at high temperature using high temperature chemical vapor deposition process. <i>Journal of Crystal Growth</i> , 2011 , 335, 17-24	1.6	17
79	From Si nanowire to SiC nanotube. <i>Journal of Nanoparticle Research</i> , 2011 , 13, 5425-5433	2.3	22
78	Aluminum nitride homoepitaxial growth on polar and non-polar AlN PVT substrates by high temperature CVD (HTCVD). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2019-2021		11
77	Kinetics of the 3C-6H polytypic transition in 3C-SiC single crystals: A diffuse X-ray scattering study. <i>Journal of Applied Physics</i> , 2011 , 110, 053508	2.5	13
76	Large area quasi-free standing monolayer graphene on 3C-SiC(111). <i>Applied Physics Letters</i> , 2011 , 99, 081904	3.4	54
75	Morphological instabilities induced by foreign particles and Ehrlich-Schwoebel effect during the two-dimensional growth of crystalline Ti ₃ SiC ₂ . <i>Physical Review B</i> , 2011 , 83,	3.3	18
74	Quality Investigation of 3C-SiC Crystals Grown by CF-PVT Technique. <i>Materials Science Forum</i> , 2011 , 679-680, 20-23	0.4	
73	TEM and LTPL Investigations of 3C-SiC Layers Grown by LPE on (100) and (111) 3C-SiC Seeds. <i>Materials Science Forum</i> , 2010 , 645-648, 383-386	0.4	1
72	Characterization and modelling of the ion-irradiation induced disorder in 6H-SiC and 3C-SiC single crystals. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 455408	3	74
71	Improvements of the Continuous Feed-Physical Vapor Transport Technique (CF-PVT) for the Seeded Growth of 3C-SiC Crystals. <i>Materials Science Forum</i> , 2010 , 645-648, 63-66	0.4	2
70	Further Evidence of Nitrogen Induced Stabilization of 3C-SiC Polytype during Growth from a Si-Ge Liquid Phase. <i>Materials Science Forum</i> , 2010 , 645-648, 163-166	0.4	3
69	Is the Liquid Phase a Viable Approach for Bulk Growth of 3C-SiC?. <i>Materials Science Forum</i> , 2010 , 645-648, 67-70	0.4	5
68	Study of the Spontaneous Nucleation of 3C-SiC Single Crystals Using CF-PVT Technique. <i>Materials Science Forum</i> , 2010 , 645-648, 55-58	0.4	3
67	Heavily p-Type Doping of Bulk 6H-SiC and 3C-SiC Grown from Al-Si Melts. <i>Materials Science Forum</i> , 2010 , 645-648, 59-62	0.4	3
66	Coupled heat transfer and fluid dynamics modeling of high-temperature SiC solution growth. <i>Journal of Crystal Growth</i> , 2010 , 312, 155-163	1.6	49
65	Evolution of 3C-SiC islands nucleated from a liquid phase on Si face SiC substrates. <i>Thin Solid Films</i> , 2010 , 518, 4234-4241	2.2	5

64	Micropipe-induced birefringence in 6H silicon carbide. <i>Journal of Applied Crystallography</i> , 2010 , 43, 122-133	133	15
63	Quantitative analysis of diffuse X-ray scattering in partially transformed 3C-SiC single crystals. <i>Journal of Applied Crystallography</i> , 2010 , 43, 867-875	3.8	8
62	The 3C-6H polytypic transition in SiC as revealed by diffuse x-ray scattering. <i>Applied Physics Letters</i> , 2009 , 94, 201904	3.4	13
61	Influence of the N/Al Ratio in the Gas Phase on the Growth of AlN by High Temperature Chemical Vapor Deposition (HTCVD). <i>Materials Science Forum</i> , 2009 , 615-617, 987-990	0.4	2
60	High-speed Growth and Characterization of Polycrystalline AlN Layers by High Temperature Chemical Vapor Deposition (HTCVD). <i>ECS Transactions</i> , 2009 , 25, 323-326	1	3
59	Optical Investigation of Electronic Properties in Bulk and Surface Region of Sublimation-Grown 3C-SiC Crystals. <i>Materials Science Forum</i> , 2009 , 615-617, 303-306	0.4	8
58	Dislocation-Induced Birefringence in Silicon Carbide. <i>Materials Science Forum</i> , 2009 , 615-617, 271-274	0.4	
57	Top Seeded Solution Growth of 3C-SiC Single Crystals. <i>Materials Science Forum</i> , 2009 , 615-617, 41-44	0.4	6
56	Nitrogen Doping of 3C-SiC Single Crystals Grown by CF-PVT. <i>Materials Science Forum</i> , 2009 , 615-617, 45-48	0.4	1
55	Effects of Temperature and Heating Rate on the Precipitation of 3C-SiC Islands on 4H-SiC(0001) from a Liquid Phase. <i>Materials Science Forum</i> , 2009 , 615-617, 193-196	0.4	
54	Defect-induced polytype transformations in LPE grown SiC epilayers on (1 1 1) 3C-SiC seeds grown by VLS on 6H-SiC. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4727-4730	2.8	1
53	A TEM study of in-grown stacking faults in 3C-SiC layers grown by CF-PVT on 4H-SiC substrates. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4749-4751	2.8	7
52	Study of the 3C-SiC nucleation from a liquid phase on a C face 6H-SiC substrate. <i>Journal of Crystal Growth</i> , 2009 , 311, 2385-2390	1.6	16
51	Thermodynamic and experimental investigations on the growth of thick aluminum nitride layers by high temperature CVD. <i>Journal of Crystal Growth</i> , 2009 , 311, 3371-3379	1.6	23
50	Nucleation and Growth of 3C-SiC Single Crystals from the Vapor Phase. <i>Materials Science Forum</i> , 2009 , 615-617, 31-36	0.4	15
49	Growth of Thick AlN Layers by High Temperature CVD (HTCVD). <i>Materials Science Forum</i> , 2008 , 600-603, 1269-1272	0.4	4
48	Structural Characterization of CF-PVT Grown Bulk 3C-SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 67-70	0.4	1
47	Comparative Study of Differently Grown 3C-SiC Single Crystals with Birefringence Microscopy. <i>Materials Science Forum</i> , 2008 , 600-603, 71-74	0.4	2

46	Silicon Carbide Growth:C/Si Ratio Evaluation and Modeling. <i>Materials Science Forum</i> , 2008 , 600-603, 83-88.4		
45	Experimental investigation of different configurations for the seeded growth of SiC crystals via a VLS mechanism. <i>Crystal Research and Technology</i> , 2008 , 43, 374-380	1.3	1
44	Prospects for 3C-SiC bulk crystal growth. <i>Journal of Crystal Growth</i> , 2008 , 310, 976-981	1.6	35
43	Characterization of stacking faults in thick 3C-SiC crystals using high-resolution diffuse X-ray scattering. <i>Journal of Crystal Growth</i> , 2008 , 310, 982-987	1.6	7
42	Status of SiC bulk growth processes. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 6150-6158	3	21
41	High SiC Growth Rate Obtained by Vapour-Liquid-Solid Mechanism. <i>Materials Science Forum</i> , 2007 , 556-557, 105-108	0.4	4
40	How to Grow 3C-SiC Single Domain on 6H-SiC(0001) by Vapor-Liquid-Solid Mechanism. <i>Materials Science Forum</i> , 2007 , 556-557, 187-190	0.4	3
39	Mechanism of Orientation Selection for the Growth Of (111) Twin Boundary Free 3C-SiC Single Crystals on Hexagonal Basis. <i>Materials Science Forum</i> , 2007 , 556-557, 199-202	0.4	
38	Thermodynamic Aspects of the Growth of SiC Single Crystals using the CF-PVT Process. <i>Chemical Vapor Deposition</i> , 2006 , 12, 541-548		14
37	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 2		
36	Characterization of Bulk 3C-SiC Single Crystals Grown on 4H-SiC by the CF-PVT Method. <i>Materials Science Forum</i> , 2006 , 527-529, 99-102	0.4	12
35	Gas Fed Top-Seeded Solution Growth of Silicon Carbide. <i>Materials Science Forum</i> , 2006 , 527-529, 111-114.4	0.4	2
34	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. <i>Materials Science Forum</i> , 2006 , 527-529, 287-290	0.4	6
33	In Situ Observation of Mass Transfer in the CF-PVT Growth Process by X-Ray Imaging. <i>Materials Science Forum</i> , 2006 , 527-529, 63-66	0.4	2
32	X-ray diffuse scattering from stacking faults in thick 3C-SiC single crystals. <i>Applied Physics Letters</i> , 2006 , 89, 091902	3.4	25
31	Growth of AlN and AlN-SiC Solid Solution by Sublimation Method. <i>Materials Science Forum</i> , 2006 , 527-529, 1501-1504	0.4	1
30	Characterization of a 3C-SiC Single Domain Grown on 6H-SiC(0001) by a Vapor-Liquid-Solid Mechanism. <i>Crystal Growth and Design</i> , 2006 , 6, 2598-2602	3.5	27
29	High-Temperature Nucleation of Cubic Silicon Carbide on (0001) Hexagonal-SiC Nominal Surfaces. <i>Crystal Growth and Design</i> , 2006 , 6, 2788-2794	3.5	26

28	High temperature processing of poly-SiC substrates from the vapor phase for wafer-bonding. <i>Surface and Coatings Technology</i> , 2006 , 201, 4014-4020	4.4	4
27	Large Area DPB Free (111) SiC Thick Layer Grown on (0001) SiC Nominal Surfaces by the CF-PVT Method. <i>Materials Science Forum</i> , 2005 , 483-485, 225-228	0.4	24
26	Control of the Supersaturation in the CF-PVT Process for the Growth of Silicon Carbide Crystals: Research and Applications. <i>Crystal Growth and Design</i> , 2005 , 5, 1539-1544	3.5	38
25	Progress and Limits of the Numerical Simulation of SiC Bulk and Epitaxy Growth Processes. <i>Materials Science Forum</i> , 2005 , 483-485, 3-8	0.4	3
24	Study of 3C-SiC nucleation on (0 0 0 1) 6H-SiC nominal surfaces by the CF-PVT method. <i>Journal of Crystal Growth</i> , 2005 , 275, e609-e613	1.6	12
23	Characterization of Thick 2-Inch 4H-SiC Layers Grown by the Continuous Feed-Physical Vapor Transport Method. <i>Materials Science Forum</i> , 2004 , 457-460, 91-94	0.4	6
22	In Situ SiC Feeding by Chemical Vapor Deposition for Bulk Growth. <i>Materials Science Forum</i> , 2004 , 457-460, 139-142	0.4	
21	Wettability Study of SiC in Correlation with XPS Analysis. <i>Materials Science Forum</i> , 2004 , 457-460, 423-426	0.4	2
20	Comparison between Various Chemical Systems for the CVD Step in the CF-PVT Crystal Growth Method. <i>Materials Science Forum</i> , 2004 , 457-460, 135-138	0.4	2
19	Electron Back Scattering Diffraction (EBSD) as a Tool for the Investigation of 3C-SiC Nucleation and Growth on 6H or 4H. <i>Materials Science Forum</i> , 2004 , 457-460, 387-390	0.4	10
18	Vapor phase techniques for the fabrication of homoepitaxial layers of silicon carbide: process modeling and characterization. <i>Applied Surface Science</i> , 2003 , 212-213, 177-183	6.7	3
17	Continuous Feed Physical Vapor Transport. <i>Journal of the Electrochemical Society</i> , 2003 , 150, G653	3.9	25
16	SiC Homoepitaxial Growth at Low Temperature by Vapor-Liquid-Solid Mechanism in AlBi Melt. <i>Crystal Growth and Design</i> , 2003 , 3, 285-287	3.5	11
15	A Study of HTCVD Renewing of the SiC Polycrystalline Source during the PVT Process. <i>Materials Science Forum</i> , 2003 , 433-436, 87-90	0.4	1
14	Heat Transfer Modeling of a New Crystal Growth Process. <i>Materials Science Forum</i> , 2003 , 433-436, 103-106	0.4	1
13	Investigation of Defects in 4H-SiC by Synchrotron Topography, Raman Spectroscopy Imaging and Photoluminescence Spectroscopy Imaging. <i>Materials Science Forum</i> , 2003 , 433-436, 265-268	0.4	2
12	Towards a Continuous Feeding of the PVT Growth Process: an Experimental Investigation. <i>Materials Science Forum</i> , 2003 , 433-436, 25-28	0.4	2
11	A comprehensive study of SiC growth processes in a VPE reactor. <i>Thin Solid Films</i> , 2002 , 402, 83-89	2.2	43

10	VapourLiquidSolid mechanism for the growth of SiC homoepitaxial layers by VPE. <i>Journal of Crystal Growth</i> , 2002 , 234, 63-69	1.6	12
9	Study of the interaction between graphite and Al-Si melts for the growth of crystalline silicon carbide. <i>Journal of Materials Science</i> , 2002 , 37, 3299-3306	4.3	17
8	Effect of the Si Droplet Size on the VLS Growth Mechanism of SiC Homoepitaxial Layers. <i>Materials Science Forum</i> , 2002 , 389-393, 287-290	0.4	10
7	Atomic-Step Observations on 6H- and 15R-SiC Polished Surfaces. <i>Materials Science Forum</i> , 2002 , 389-393, 729-732	0.4	11
6	Thermochemistry of silicon carbide growth by chemical transport reactions. <i>Journal of Materials Science</i> , 2001 , 36, 335-342	4.3	3
5	Aluminium-Silicon as a Melt for the Low Temperature Growth of SiC Crystals. <i>Materials Science Forum</i> , 2001 , 353-356, 85-90	0.4	9
4	3C-SiC Pseudosubstrates for the Growth of Cubic GaN. <i>Materials Science Forum</i> , 2000 , 338-342, 1467-1470	0.4	4
3	Growth Mode and Kinetics of Atmospheric Pressure Chemical Vapour Deposition of SiC on Si(100) Substrate. <i>Materials Science Forum</i> , 1998 , 264-268, 227-230	0.4	9
2	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. <i>Materials Science Forum</i> , 2004 , 287-290	0.4	3
1	Chemical Vapor Deposition of 3C-SiC on [100] Oriented Silicon at Low Temperature < 1200°C for Photonic Applications. <i>Materials Science Forum</i> , 2002 , 1062, 119-124	0.4	1